

# **µPA602CT** N-CHANNEL MOSFET FOR SWITCHING

R07DS1282EJ0200 Rev.2.00 Jul 10, 2015

# Description

The UPA602CT, N-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.5 V power source.

# Features

- Two MOSFET circuits
- Directly driven by a 4.5 V power source.
- Low on-state resistance

 $R_{DS(on)1} = 2.7 \Omega MAX. (V_{GS} = 10 V, I_D = 100 mA)$  $R_{DS(on)2} = 3.2 \Omega MAX. (V_{GS} = 4.5 V, I_D = 50 mA)$ 

## **Ordering Information**

Part Number	Lead Plating	Packing	Package	
UPA602CT-T1-A/AT	-A : Sn-Bi , -AT : Pure Sn	3000p/Reel	SC-74 (6pMM)	

Remark "-AT" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

## Marking UB

# Absolute Maximum Ratings (T<sub>A</sub> = 25°C)

Drain to Source Voltage ( $V_{GS}$ = 0 V)	Vdss	60	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	V <sub>GSS</sub>	±20	V
Drain Current (DC)	ID(DC)	±100	mA
Drain Current (pulse) <sup>Note</sup>	D(pulse)	±200	mA
Total Power Dissipation	Рт	300 (Total)	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

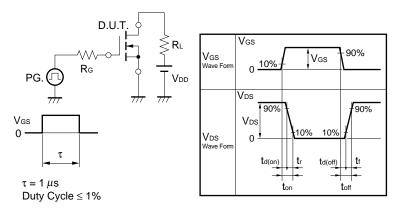


# Electrical Characteristics (T<sub>A</sub> = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μA
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		2.5	V
Forward Transfer Admittance Note	y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 mA	150			mS
Drain to Source On-state Resistance <sup>Note</sup>	RDS(on)1	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA		2.1	2.7	Ω
	RDS(on)2	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 mA		2.4	3.2	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V,		20		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V,		9		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		2		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = 10 V,		16		ns
Rise Time	tr	I⊳ = 200 mA,		6.5		ns
Turn-off Delay Time	td(off)	V <sub>GS</sub> = 10 V,		82		ns
Fall Time	tr	R <sub>G</sub> = 10 Ω		32		ns
Total Gate Charge	QG	I <sub>D</sub> = 200 mA, V <sub>DD</sub> = 25 V, V <sub>GS</sub> = 10 V		2		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 200 mA, VGS = 0 V		0.86		V

Note Pulsed

# **Test Circuit Switching Time**

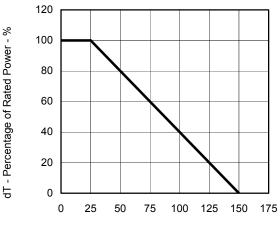




Ip - Drain Current - mA

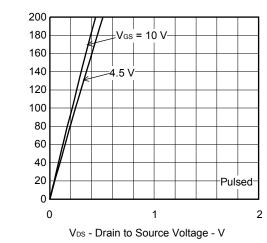
# Typical Characteristics (T<sub>A</sub> = 25°C)

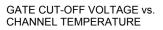
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

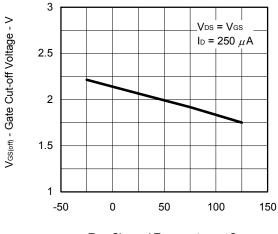


 $T_A-Ambient\ Temperature\ -\ ^\circ C$ 



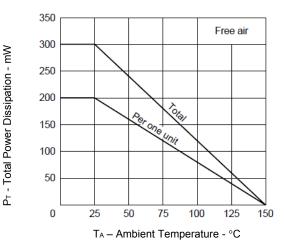




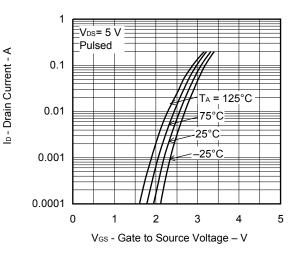


Tch - Channel Temperature - °C

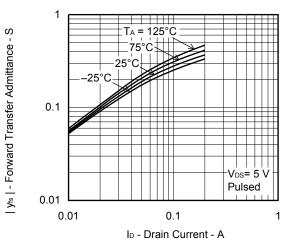
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



### FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



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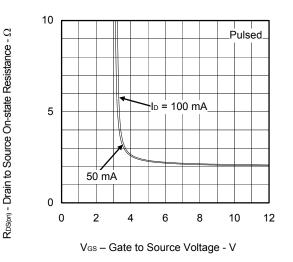


DRAIN CURRENT

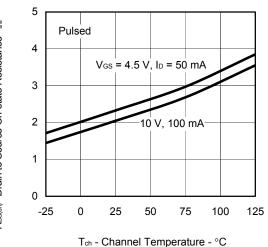
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DRAIN TO SOURCE ON-STATE RESISTANCE vs.

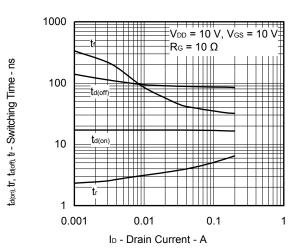
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



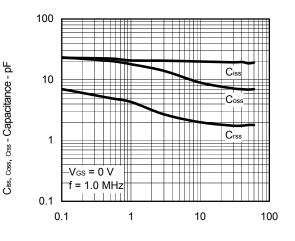
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

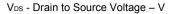




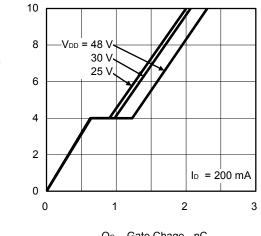








### DYNAMIC INPUT CHARACTERISTICS



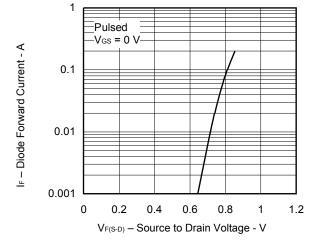
 $R_{\text{DS(on)}}$  - Drain to Source On-state Resistance -  $\Omega$ 

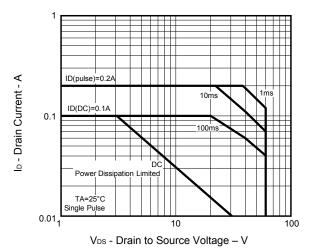


V<sub>GS</sub> – Gate to Source Voltage - V

## SOURCE TO DRAIN DIODE FORWARD VOLTAGE

## FORWARD BIAS SAFE OPERATING AREA

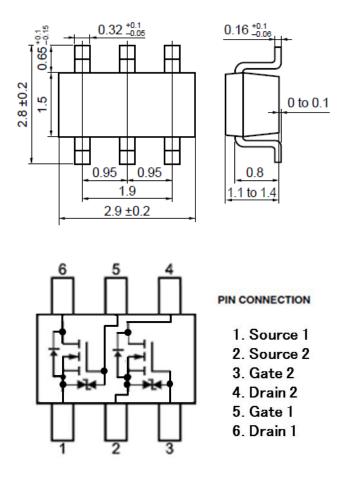




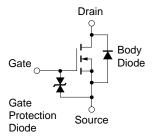


# Package Drawings (Unit: mm)

# SC-74 (6pMM)



# **Equivalent Circuit**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.



μPA602CT
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		Description		
Rev.	Date	Page	Summary	
1.00	Sep , 2013	_	First Edition Issued	
2.00	Jun, 2015	2	- Changed Electrical Characteristics	
			- Changed Test Circuit Switching Time	
		3, 4, 5	Changed all graphs	

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